

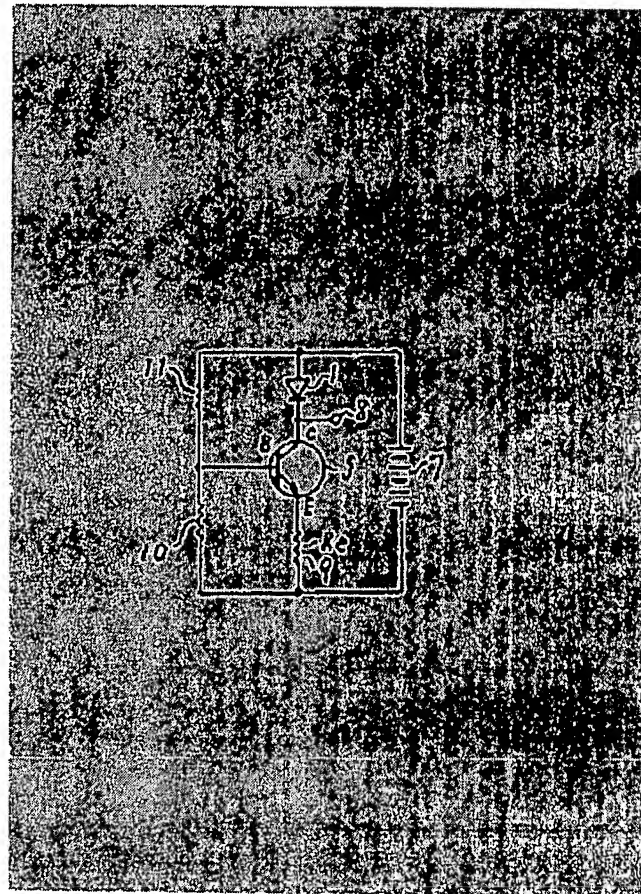
BIAS CIRCUIT FOR LASER DIODE

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Abstract of JP55115383

PURPOSE: To stabilize a light output despite the change in the threshold current of a laser diode due to temperature change, by utilizing the voltage across the base and emitter of a transistor or the temperature characteristics of said voltage and the terminal voltage of the diode. **CONSTITUTION:** A laser diode 1 is connected to the collector of a transistor 5 through a modulation signal input terminal 8. A resistor 9 whose resistance is set for temperature compensation is coupled to the emitter of the transistor. Bias resistors 10, 11 for the transistor 5 are coupled in parallel with the connected circuit including the transistor and the diode 1. The connection node of the resistors 10, 11 is connected to the base of the transistor 5. A DC power source 7 is coupled in parallel with the circuit including the transistor 5. Since the light output of the diode is stabilized by the temperature characteristic of the transistor circuit against the ambient temperature, the bias circuit is rendered simple and cheap.



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